



# FUKUCOM COMPANY LTD.

福 靈 有 限 公 司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,  
KWUN TONG, KOWLOON, HONG KONG.

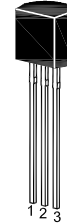
TEL: 852-2790 0314 FAX: 852-2790 0206

## ST 2SC2383

### NPN Silicon Epitaxial Planar Transistor

The transistor is subdivided into three groups, R, O and Y, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



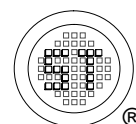
1. Emitter 2. Collector 3. Base  
TO-92 Plastic Package

#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{CBO}$	160	V
Collector Emitter Voltage	$V_{CEO}$	160	V
Emitter Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	1	A
Base Current	$I_B$	0.5	A
Collector Power Dissipation	$P_{tot}$	900	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 55 to + 150	$^\circ\text{C}$

#### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$ , $I_C = 200\text{ mA}$ Current Gain Group	R $h_{FE}$	60	-	120	-
	O $h_{FE}$	100	-	200	-
	Y $h_{FE}$	160	-	320	-
Collector Base Cutoff Current at $V_{CB} = 150\text{ V}$	$I_{CBO}$	-	-	1	$\mu\text{A}$
Emitter Base Cutoff Current at $V_{EB} = 6\text{ V}$	$I_{EBO}$	-	-	1	$\mu\text{A}$
Collector Emitter Breakdown Voltage at $I_C = 10\text{ mA}$	$V_{(BR)CEO}$	160	-	-	V
Collector Emitter Saturation Voltage at $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$	$V_{CE(sat)}$	-	-	1.5	V
Base Emitter Voltage at $I_C = 5\text{ mA}$ , $V_{CE} = 5\text{ V}$	$V_{BE}$	0.45	-	0.75	V
Transition Frequency at $V_{CE} = 5\text{ V}$ , $I_C = 200\text{ mA}$	$f_T$	20	100	-	MHz
Collector Output Capacitance at $V_{CB} = 10\text{ V}$ , $f = 1\text{ MHz}$	$C_{ob}$	-	-	20	pF





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